

General Description

The WST2N7002K is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST2N7002K meet the RoHS and Green Product requirement with full function reliability approved.

Features

- High-speed switching
- Green Device Available
- ESD Protected:2KV

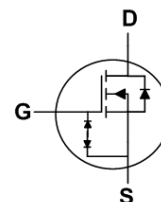
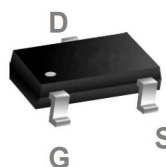
Product Summary

| BVDSS | RDSON | ID |
|-------|-------|-------|
| 60V | 1Ω | 300mA |

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC
- Networking DC-DC Power System
- Load Switch

SOT-23N Pin Configuration



Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|----------------------|--|------------|------------|
| V_{DS} | Drain-Source Voltage | 60 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D@T_A=25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V^1$ | 300 | mA |
| $I_D@T_A=70^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V^1$ | 150 | mA |
| I_{DM} | Pulsed Drain Current ² | 1.2 | A |
| $P_D@T_A=25^\circ C$ | Total Power Dissipation ³ | 0.2 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ C$ |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|-----------------|--|------|------|--------------|
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient ¹ | --- | 625 | $^\circ C/W$ |

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------------|--|---|------|------|------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250uA | 60 | --- | --- | V |
| ΔBV _{DSS} /ΔT _J | BV _{DSS} Temperature Coefficient | Reference to 25°C, I _D =1mA | --- | 0.05 | --- | V/°C |
| R _{DS(ON)} | Static Drain-Source On-Resistance ² | V _{GS} =10V, I _D =0.5A | --- | 1 | 3 | Ω |
| | | V _{GS} =4.5V, I _D =0.2A | --- | 4 | 5 | |
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =250uA | 1 | --- | 2.5 | V |
| ΔV _{GS(th)} | V _{GS(th)} Temperature Coefficient | | --- | -3.7 | --- | mV/°C |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =60V, V _{GS} =0V, T _J =25°C | --- | --- | 1 | uA |
| | | V _{DS} =60V, V _{GS} =0V, T _J =55°C | --- | --- | 5 | |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±20V, V _{DS} =0V | --- | --- | ±10 | uA |
| g _{fs} | Forward Transconductance | V _{DS} =5V, I _D =0.3A | --- | 300 | --- | mS |
| T _{d(on)} | Turn-On Delay Time | V _{DD} =30V, V _{GS} =10V, R _G =3.3Ω, I _D =0.5A | --- | 15 | 6 | ns |
| T _r | Rise Time | | --- | 35 | 3.3 | |
| T _{d(off)} | Turn-Off Delay Time | | --- | 35 | 16 | |
| T _f | Fall Time | | --- | 35 | 13.6 | |
| C _{iSS} | Input Capacitance | V _{DS} =25V, V _{GS} =0V, f=1MHz | --- | 32 | 56 | pF |
| C _{oSS} | Output Capacitance | | --- | 7 | 17 | |
| C _{rSS} | Reverse Transfer Capacitance | | --- | 3 | 10.6 | |

Diode Characteristics

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-----------------|--|---|------|------|------|------|
| I _S | Continuous Source Current ^{1,4} | V _G =V _D =0V, Force Current | --- | --- | 300 | mA |
| I _{SM} | Pulsed Source Current ^{2,4} | | --- | --- | 1.2 | A |
| V _{SD} | Diode Forward Voltage ² | V _{GS} =0V, I _S =1A, T _J =25°C | --- | --- | 1 | V |

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature.
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

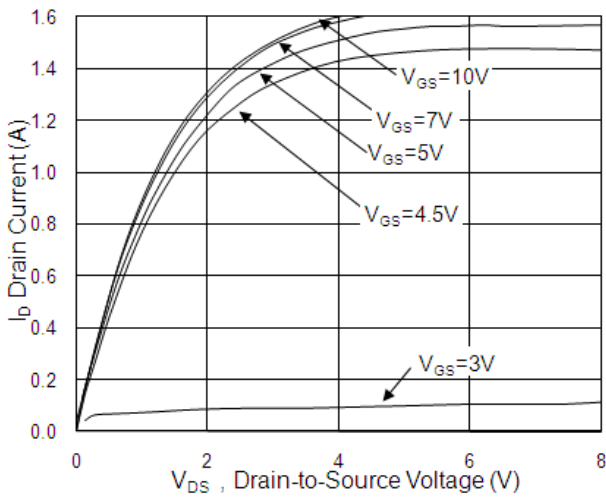


Fig.1 Typical Output Characteristics

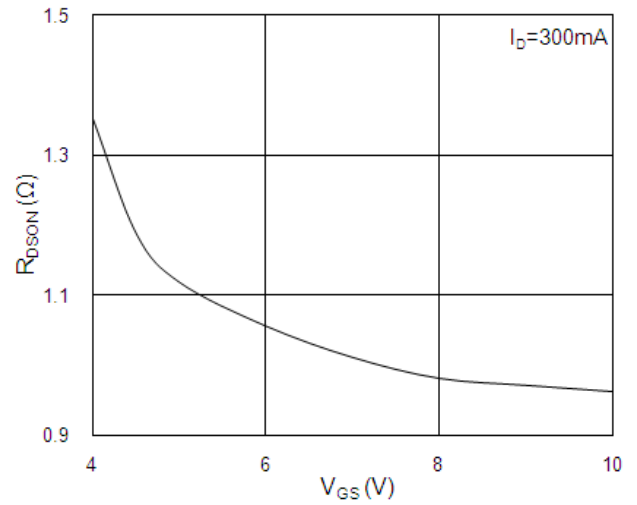


Fig.2 On-Resistance vs. Gate-Source Voltage

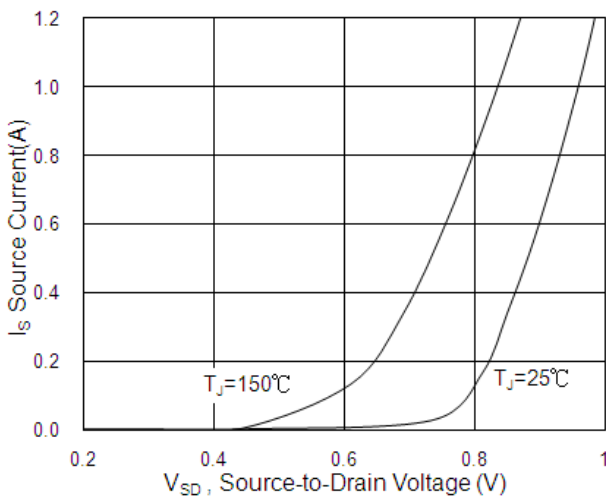


Fig.3 Forward Characteristics of Reverse

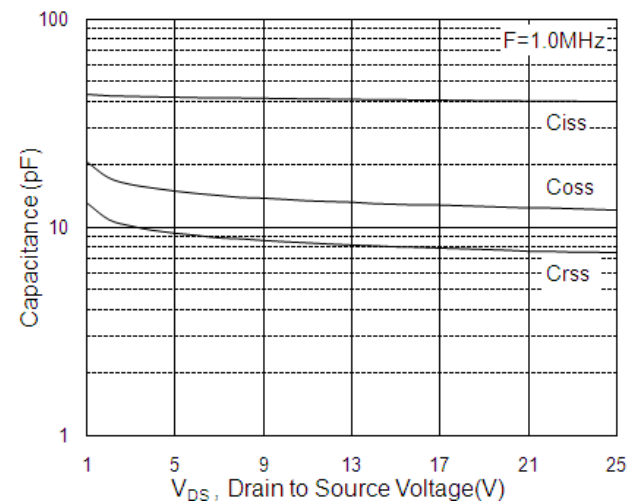


Fig.4 Capacitance

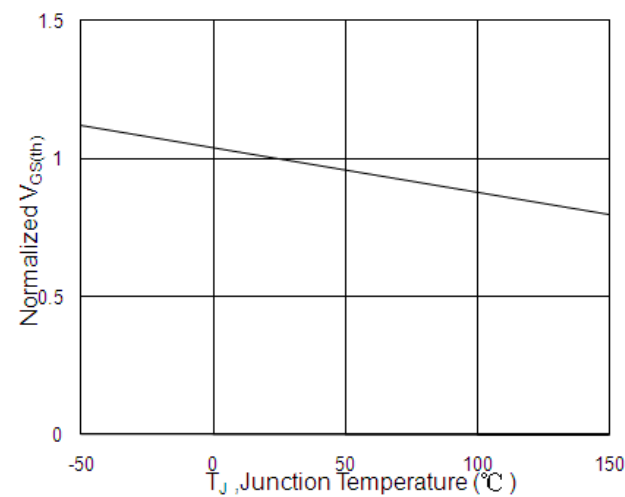


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

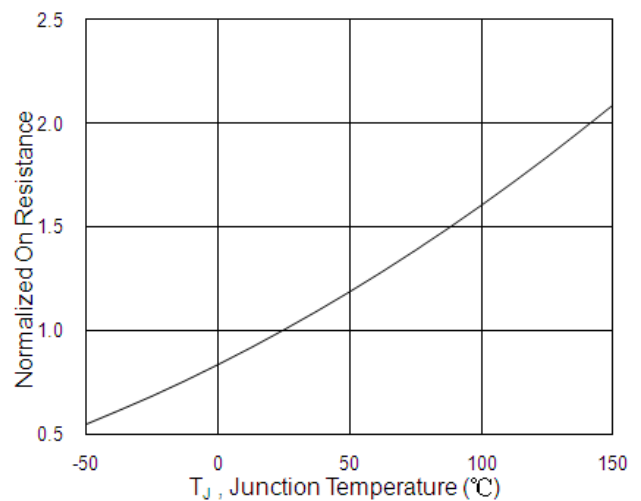


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

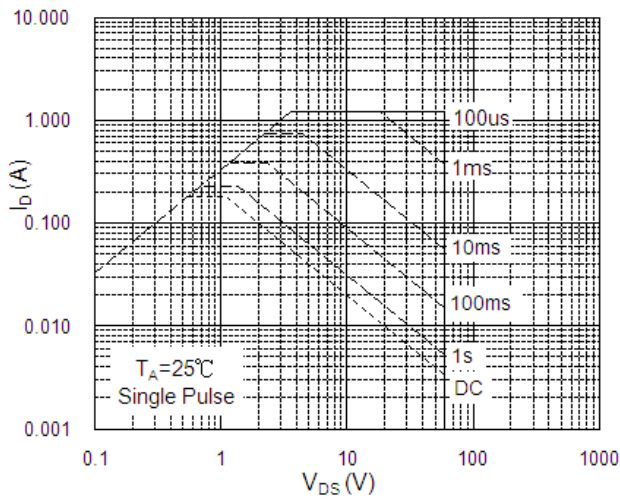


Fig.8 Safe Operating Area

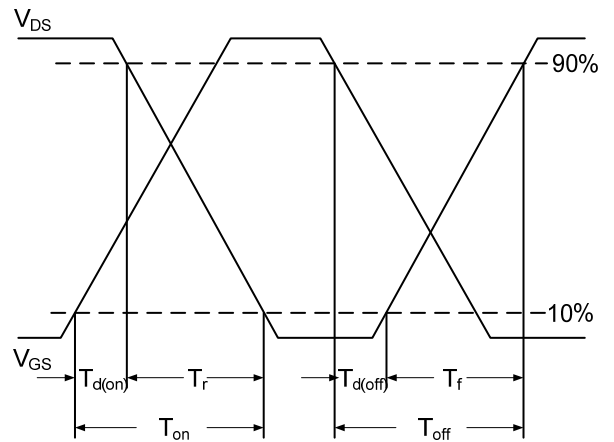


Fig.10 Switching Time Waveform

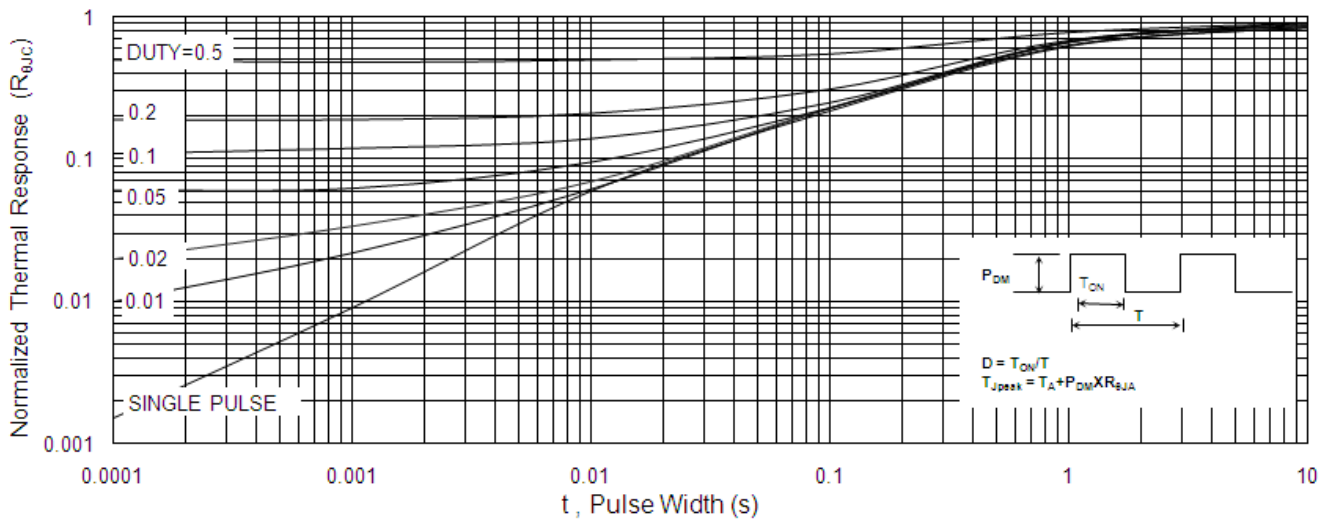


Fig.9 Normalized Maximum Transient Thermal Impedance



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